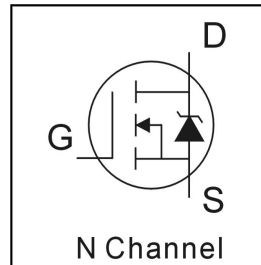


N Channel Power MOSFET with extremely low RDS(on)

Chip Specification

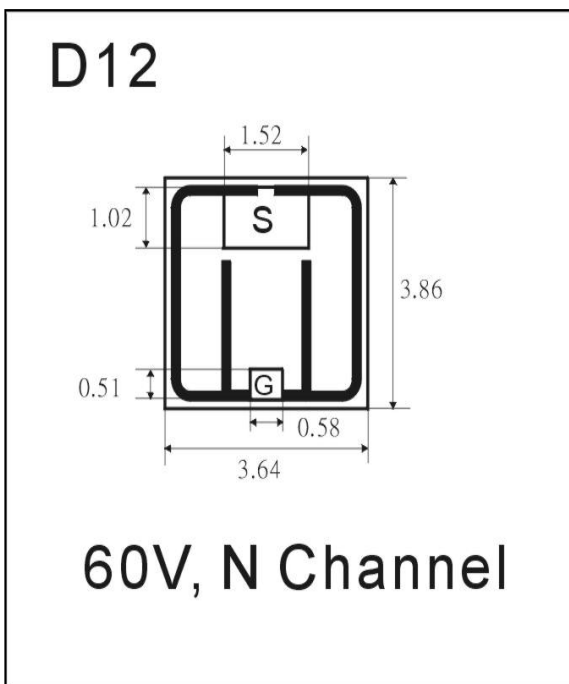
General Description:

- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * **175°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**
- * **extremely low RDS(ON)**



Mechanical Data:

D12	
Dimension	3.64mm x 3.86mm
Thickness:	400 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
	95/5 PbSn or 92.5./2.5/5 PbAgIn
Source Bonding Wire:	15 mil Al



Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	60	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.05	Ω	VGS=10V, ID=16A
Continuous Drain current (in target package)	ID@25°C	26	A	VGS=10V
Continuous Drain current (in target package)	ID@100°C	18	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

Target Device: IRFZ34

TO-220AB

PD

56

W

@Tc=25°C

